LMX2335L 1.1 GHz/1.1 GHz
LMX2336L 2.0 GHz/1.1GHz
PLLatinum™ Low Power Dual Frequency Synthesizer for RF Personal Communications

Check for Samples: LMX2335L, LMX2336L

FEATURES

- **Ultra Low Current Consumption**
- **2.7V to 5.5V Operation**
- **Selectable Synchronous and Asynchronous Powerdown Mode:**
  - **I_{CC} = 1 µA (Typ)**
- **Dual Modulus Prescaler: 64/65 or 128/129**
- **Selectable Charge Pump TRI-STATE Mode**
- **Selectable Charge Pump Current Levels**
- **Selectable Fastlock Mode**
- **Upgrade and Compatible to LMX2335/36**
- **Small-Outline, Plastic, Surface Mount TSSOP Package**
- **LMX2336 Available in LGA Package**

APPLICATIONS

- **Cellular Telephone Systems (AMPS, ETACS, RCR-27)**
- **Cordless Telephone Systems**
  - **(DECT, ISM, PHS, CT-1+)**
- **Personal Communication Systems**
  - **(DCS-1800, PCN-1900)**
- **Dual Mode PCS Phones**
- **Cable TV Tuners (CATV)**
- **Other Wireless Communication Systems**

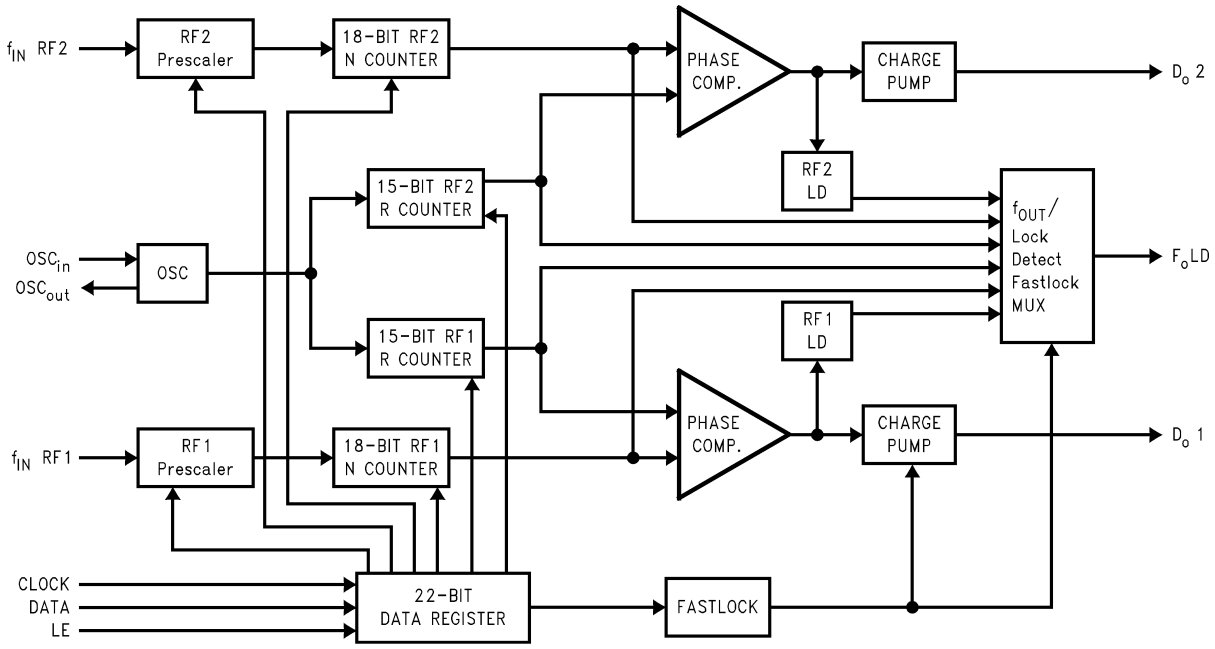
DESCRIPTION

The LMX2335L and LMX2336L are monolithic, integrated dual frequency synthesizers, including two high frequency prescalers, and are designed for applications requiring two RF phase-lock loops. They are fabricated using TI's 0.5µ ABiC V silicon BiCMOS process.

The LMX2335L/36L contains two dual modulus prescalers. A 64/65 or a 128/129 prescaler can be selected for each RF synthesizer. A second reference divider chain is included in the IC for improved system noise. The LMX2335L/36L combined with a high quality reference oscillator, two loop filters, and two external voltage controlled oscillators generates very stable low noise RF local oscillator signals.

Serial data is transferred into the LMX2335L/36L via a three wire interface (Data, Enable, Clock). Supply voltage can range from 2.7V to 5.5V. The LMX2335L/36L feature very low current consumption; LMX2335L 4.0 mA at 5V, LMX2336L 5.5 mA at 5V. The LMX2335L is available in SO, TSSOP and LGA 16-pin surface mount plastic packages. The LMX2336L is available in a TSSOP 20-pin and LGA 24-pin surface mount plastic package.

Functional Block Diagram



Connection Diagram

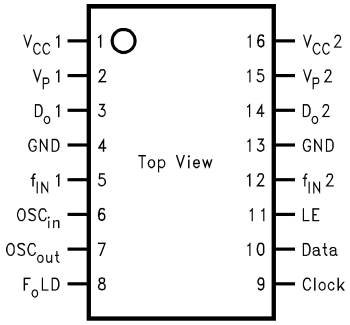


Figure 1. LMX2335L
(Top View)
See Package Number D0016A and PW0016A

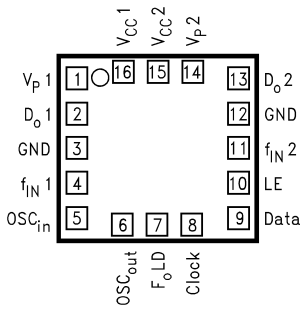


Figure 2. LMX2335L
(Top View)
See Package Number NPG0016A

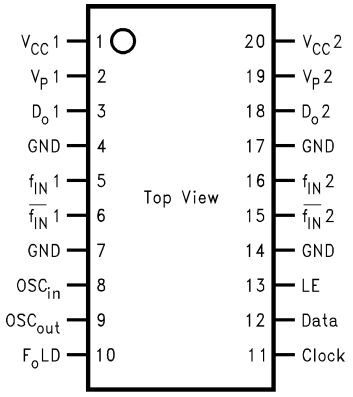


Figure 3. LMX2336L
(Top View)
See Package Number PW0020A

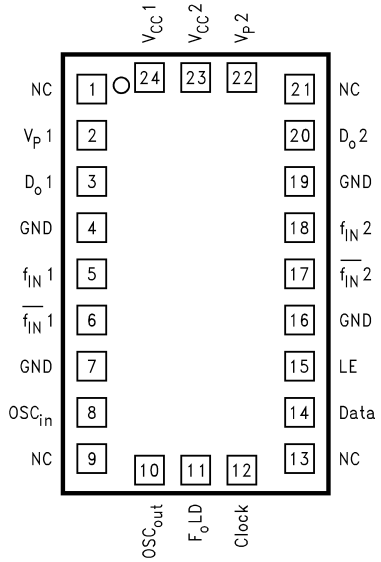


Figure 4. LMX2336L
(Top View)
See Package Number NPH0024A

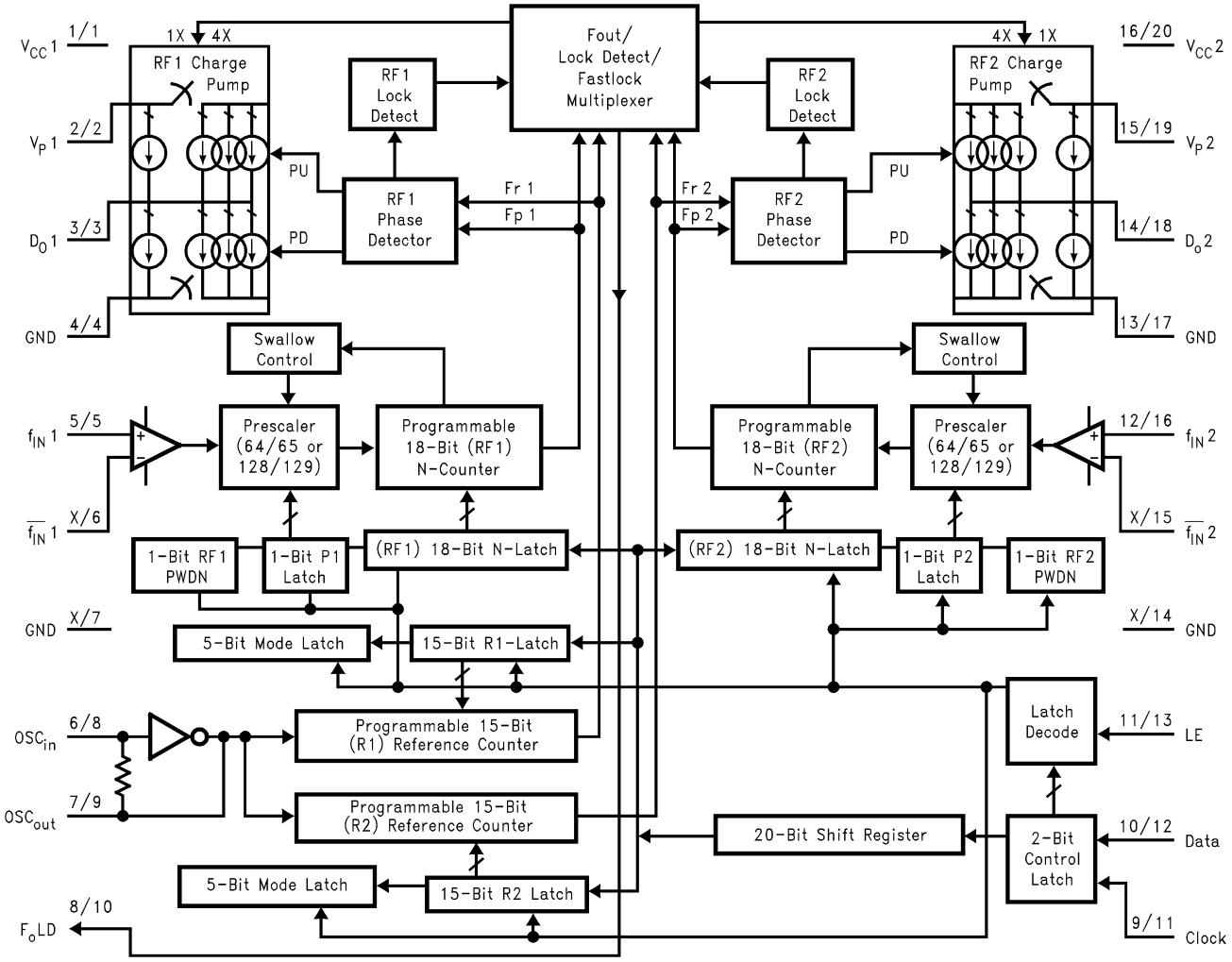
PIN DESCRIPTIONS

Pin No. 2336LPW	Pin No. 2336LNPH	Pin No. 2335LPW	Pin No. 2335LNPG	Pin Name	I/O	Description
1	24	1	16	$V_{CC}1$		Power supply voltage input for RF1 analog and RF1 digital circuits. Input may range from 2.7V to 5.5V. $V_{CC}1$ must equal $V_{CC}2$. Bypass capacitors should be placed as close as possible to this pin and be connected directly to the ground plane.
2	2	2	1	V_p1		Power supply for RF1 charge pump. Must be ≥ V_{CC}.
3	3	3	2	D_o1	O	RF1 charge pump output. For connection to a loop filter for driving the input of an external VCO.
4	4	4	3	GND		LMX2335L: Ground for RF1 analog and RF1 digital circuits. LMX2336L: Ground for RF digital circuits.
5	5	5	4	f_{IN} 1	I	RF1 prescaler input. Small signal input from the VCO.
6	6	X	X	/f_{IN} 1	I	RF1 prescaler complementary input. A bypass capacitor should be placed as close as possible to this pin and be connected directly to the ground plane. Capacitor is optional with loss of some sensitivity.
7	7	X	X	GND		Ground for RF1 analog circuitry.
8	8	6	5	OSC_{in}	I	Oscillator input. The input has a V_{CC}/2 input threshold and can be driven from an external CMOS or TTL logic gate.
9	10	7	6	OSC_{out}	O	Oscillator output.
10	11	8	7	F_oLD	O	Multiplexed output of the programmable or reference dividers, lock detect signals and Fastlock mode. CMOS output *(see Table 1)*.
11	12	9	8	Clock	I	High impedance CMOS Clock input. Data for the various latches is clocked in on the rising edge, into the 20-bit shift register.
12	14	10	9	Data	I	Binary serial data input. Data entered MSB first. The last two bits are the control bits. High impedance CMOS input.
13	15	11	10	LE	I	Load enable high impedance CMOS input. When LE goes HIGH, data stored in the shift registers is loaded into one of the 4 appropriate latches (control bit dependent).
14	16	X	X	GND		Ground for RF2 analog circuitry.
15	17	X	X	/f_{IN}2	I	RF2 prescaler complementary input. A bypass capacitor should be placed as close as possible to this pin and be connected directly to the ground plane. Capacitor is optional with loss of some sensitivity.
16	18	12	11	f_{IN} 2	I	RF2 prescaler input. Small signal input from the VCO.

PIN DESCRIPTIONS (continued)

Pin No. 2336LPW	Pin No. 2336LNPH	Pin No. 2335LPW	Pin No. 2335LNPG	Pin Name	I/O	Description
17	19	13	12	GND		LMX2335L: Ground for RF2 analog, RF2 digital, MICROWIRE, F_oLD and Oscillator circuits. LMX2336L: Ground for IF digital, MICROWIRE, F_oLD and oscillator circuits.
18	20	14	13	D_o 2	O	RF2 charge pump output. For connection to a loop filter for driving the input of an external VCO.
19	22	15	14	V_p2		Power supply for RF2 charge pump. Must be ≥ V_{CC}.
20	23	16	15	V_{CC}2		Power supply voltage input for RF2 analog, RF2 digital, MICROWIRE, F_oLD and oscillator circuits. Input may range from 2.7V to 5.5V. V_{CC}2 must equal V_{CC}1. Bypass capacitors should be placed as close as possible to this pin and be connected directly to the ground plane.
X	1, 9, 13, 21	X	X	NC		No connect.

Block Diagram



Note: $V_{CC}1$ supplies power to the RF1 prescaler, N-counter, R-counter, and phase detector. $V_{CC}2$ supplies power to the RF2 prescaler, N-counter, phase detector, R-counter along with the OSC_{in} buffer, MICROWIRE, and F_oLD. $V_{CC}1$ and $V_{CC}2$ are clamped to each other by diodes and must be run at the same voltage level.

Note: V_P1 and V_P2 can be run separately as long as $V_P \geq V_{CC}$.

Note: Pin # → 8/10 ← LMX2336L Pin #
Pin Name → F_oLD

X signifies a function not bonded out to a pin

Figure 5. LMX2335L

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1)(2)(3)

Power Supply Voltage	
V_{CC}	−0.3V to +6.5V
V_P	−0.3V to +6.5V
Voltage on Any Pin with GND = 0V (V_I)	−0.3V to V_{CC} +0.3V
Storage Temperature Range (T_S)	−65°C to +150°C
Lead Temperature (solder 4 sec.) (T_L)	+260°C

(1) This device is a high performance RF integrated circuit with an ESD rating <2 keV and is ESD sensitive. Handling and assembly of this device should only be done at ESD protected work stations.
(2) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Recommended Operating Conditions indicate conditions for which the device is intended to be functional, but do not ensure specific performance limits. For ensured specifications and test conditions, see the Electrical Characteristics. The ensured specifications apply only for the test conditions listed.
(3) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

Recommended Operating Conditions

Power Supply Voltage	
V_{CC}	2.7V to 5.5V
V_P	V_{CC} to +5.5V
Operating Temperature (T_A)	−40°C to +85°C

Electrical Characteristics

V_{CC} = 5.0V, V_P = 5.0V; T_A = 25°C, except as specified

Symbol	Parameter		Conditions	Value			Units
				Min	Typ	Max	
I_{CC}	Power Supply Current	LMX2335L RF1 and RF2	V_{CC} = 2.7V to 5.5V		4.0	5.2	mA
I_{CC}		LMX2335L RF1 only			2.0	2.6	mA
I_{CC}		LMX2336L RF1 and RF2			5.5	7	mA
		LMX2336L RF1 only			3.3	4.3	mA
f_{IN} 1	Operating Frequency	LMX2335L		0.100		1.1	GHz
f_{IN} 2				0.050		1.1	GHz
f_{IN}1		LMX2336L		0.200		2.0	GHz
f_{IN}2				0.050		1.1	GHz
$I_{CC\text{-}PWDN}$	Powerdown Current	LMX2335L/2336L	V_{CC} = 5.5V		1	10	µA
f_{OSC}	Oscillator Frequency		With resonator load on OSC_{out}	5		20	MHz
f_{OSC}			No load on OSC_{out}	5		40	MHz
f_φ	Maximum Phase Detector Frequency				10		MHz
Pf_{IN}	RF Input Sensitivity		V_{CC} = 3.0V, f > 100 MHz	−15		0	dBm
Pf_{IN}			V_{CC} = 5.0V, f > 100 MHz	−10		0	
V_{OSC}	Oscillator Sensitivity		OSC_{in}	0.5			V_{PP}
V_{IH}	High-Level Input Voltage		(1)	0.8 V_{CC}			V
V_{IL}	Low-Level Input Voltage		(1)			0.2 V_{CC}	V
I_{IH}	High-Level Input Current		V_{IH} = V_{CC} = 5.5V (1)	−1.0		1.0	µA
I_{IL}	Low-Level Input Current		V_{IL} = 0V, V_{CC} = 5.5V (1)	−1.0		1.0	µA
I_{IH}	Oscillator Input Current		V_{IH} = V_{CC} = 5.5V			100	µA
I_{IL}	Oscillator Input Current		V_{IL} = 0V, V_{CC} = 5.5V	−100			µA

(1) Clock, Data and LE does not include f_{IN}1, f_{IN}2 and OSC_{in}.

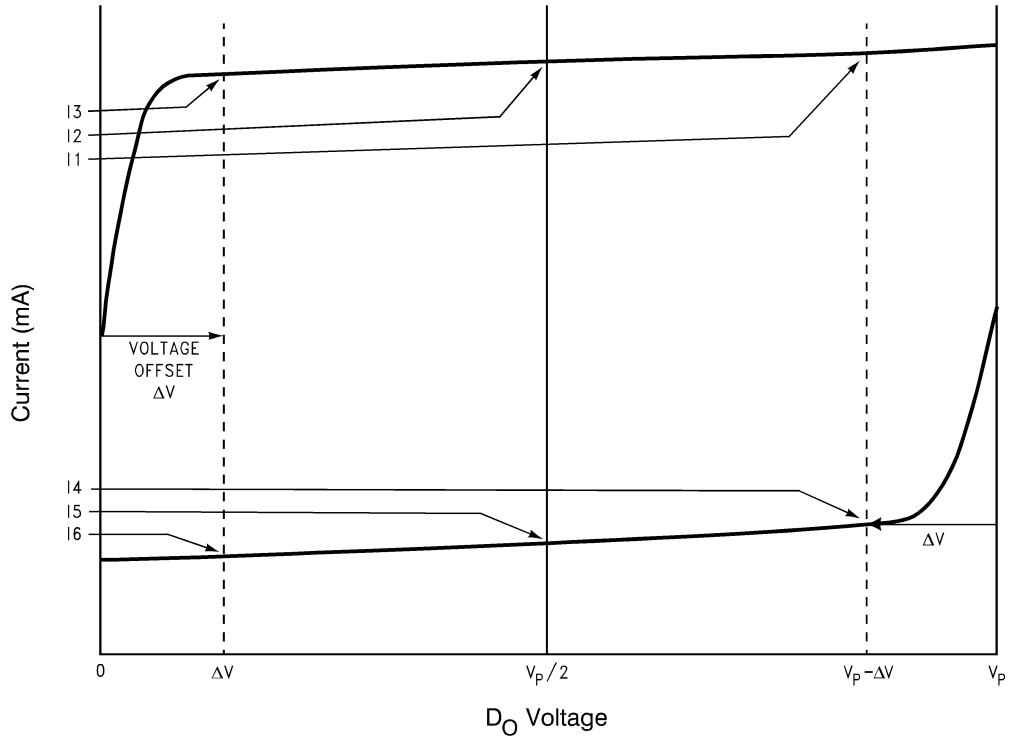
Electrical Characteristics (continued)

V_{CC} = 5.0V, V_P = 5.0V; T_A = 25°C, except as specified

Symbol	Parameter	Conditions	Value			Units
			Min	Typ	Max	
$I_{Do\text{-}SOURCE}$	Charge Pump Output Current	$V_{Do} = V_P/2$, I_{CPo} = LOW (2)		−1.25		mA
$I_{Do\text{-}SINK}$		$V_{Do} = V_P/2$, I_{CPo} = LOW (2)		1.25		mA
$I_{Do\text{-}SOURCE}$		$V_{Do} = V_P/2$, I_{CPo} = HIGH (2)		−5.00		mA
$I_{Do\text{-}SINK}$		$V_{Do} = V_P/2$, I_{CPo} = HIGH (2)		5.00		mA
$I_{Do\text{-}TRI}$	Charge Pump TRI-STATE Current	0.5V ≤ V_{Do} ≤ V_{CC} − 0.5V T_A = 25°C	−5.0		5.0	nA
$I_{Do\text{-}SINK}$ vs $I_{Do\text{-}SOURCE}$	Charge Pump Sink vs Source Mismatch	$V_{Do} = V_P/2$ T_A = 25°C (3)		3		%
I_{Do} vs V_{Do}	Charge Pump Current Vs Voltage	0.5≤ V_{DO} ≤V_p-0.5V T_A = 25°C (3)		10		%
I_{Do} vs T_A	Charge Pump Current vs Temperature	$V_{Do} = V_P/2$ -40°C≤ T_A ≤85°C (3)		10		%
V_{OH}	High-Level Output Voltage	I_{OH} = −500 µA	V_{CC} − 0.4			V
V_{OL}	Low-Level Output Voltage	I_{OL} = 500 µA			0.4	V
t_{CS}	Data to Clock Set Up Time	See SERIAL DATA INPUT TIMING	50			ns
t_{CH}	Data to Clock Hold Time	See SERIAL DATA INPUT TIMING	10			ns
t_{CWH}	Clock Pulse Width High	See SERIAL DATA INPUT TIMING	50			ns
t_{CWL}	Clock Pulse Width Low	See SERIAL DATA INPUT TIMING	50			ns
t_{ES}	Clock to Load Enable Set Up Time	See SERIAL DATA INPUT TIMING	50			ns
t_{EW}	Load Enable Pulse Width	See SERIAL DATA INPUT TIMING	50			ns

(2) See Table 1 for I_{CPo} description.
(3) See Figure 6

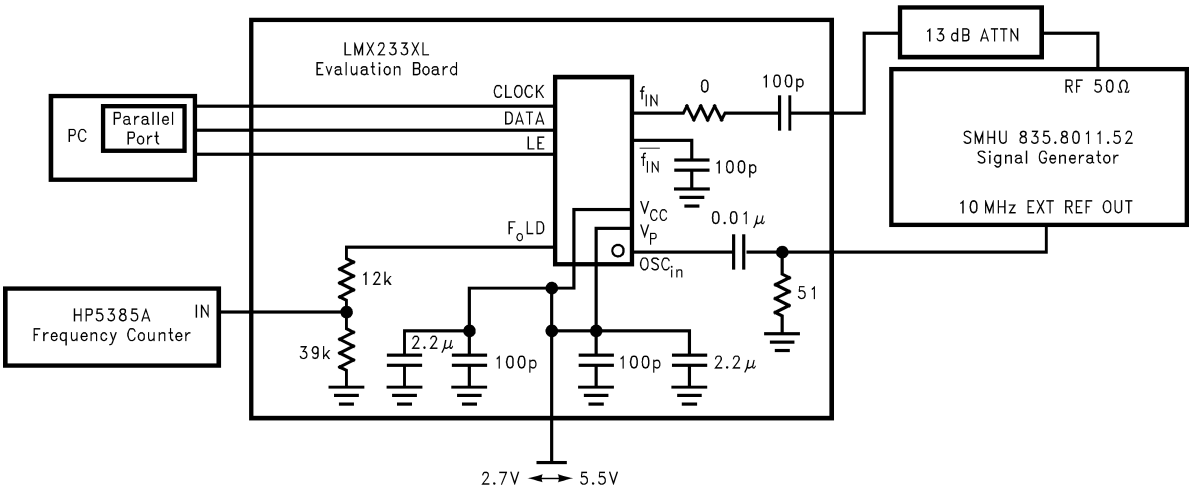
Figure 6. Charge Pump Current Specification Definitions



I1 = CP sink current at $V_{Do} = V_P - \Delta V$
I2 = CP sink current at $V_{Do} = V_P/2$
I3 = CP sink current at $V_{Do} = \Delta V$
I4 = CP source current at $V_{Do} = V_P - \Delta V$
I5 = CP source current at $V_{Do} = V_P/2$
I6 = CP source current at $V_{Do} = \Delta V$
V = Voltage offset from positive and negative rails. Dependent on VCO tuning range relative to V_{CC} and ground. Typical values are between 0.5V and 1.0V.

1. I_{Do} vs V_{Do} = Charge Pump Output Current magnitude variation vs Voltage =
   [½ * {|I1| − |I3|}]/[½ * {|I1| + |I3|}] * 100% and [½ * {|I4| − |I6|}]/[½ * {|I4| + |I6|}] * 100%
2. $I_{Do\text{-}sink}$ vs $I_{Do\text{-}source}$ = Charge Pump Output Current Sink vs Source Mismatch =
   [|I2| − |I5|]/[½ * {|I2| + |I5|}] * 100%
3. I_{Do} vs T_A = Charge Pump Output Current magnitude variation vs Temperature =
   [|I2 @ temp| − |I2 @ 25°C|]/|I2 @ 25°C| * 100% and [|I5 @ temp| − |I5 @ 25°C|]/|I5 @ 25°C| * 100%

RF Sensitivity Test Block Diagram



N = 10,000R = 50P = 64

Sensitivity limit is reached when the error of the divided RF output, F_oLD, is ≥ 1 Hz.

Typical Performance Characteristics

I_{CC} vs V_{CC} LMX2335L

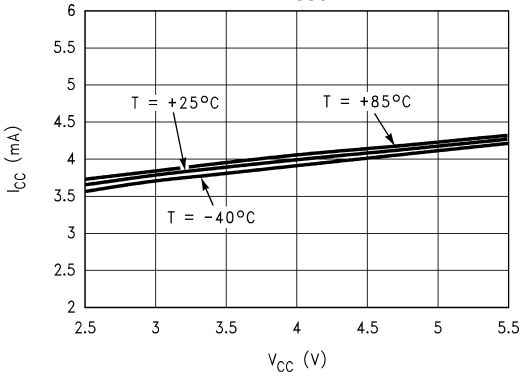


Figure 7.

I_{CC} vs V_{CC} LMX2336L

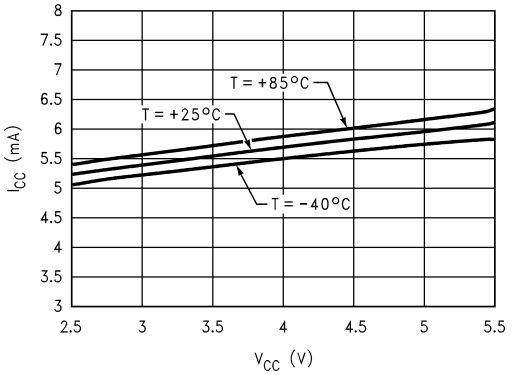


Figure 8.

Charge Pump Current vs D_o Voltage I_{cp} = HIGH

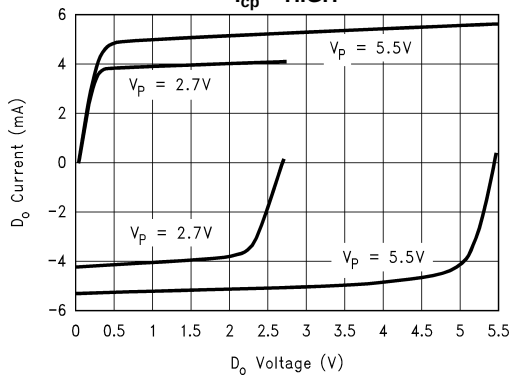


Figure 9.

Charge Pump Current vs D_o Voltage I_{cp} = LOW

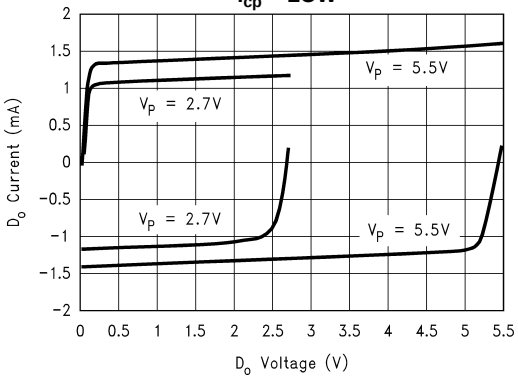
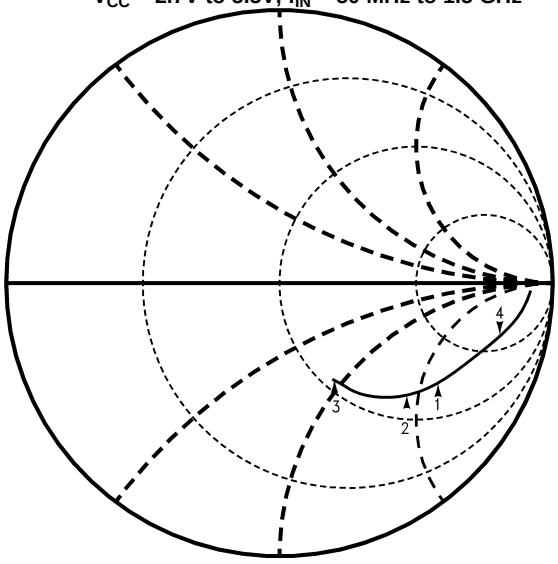


Figure 10.

Typical Performance Characteristics (continued)

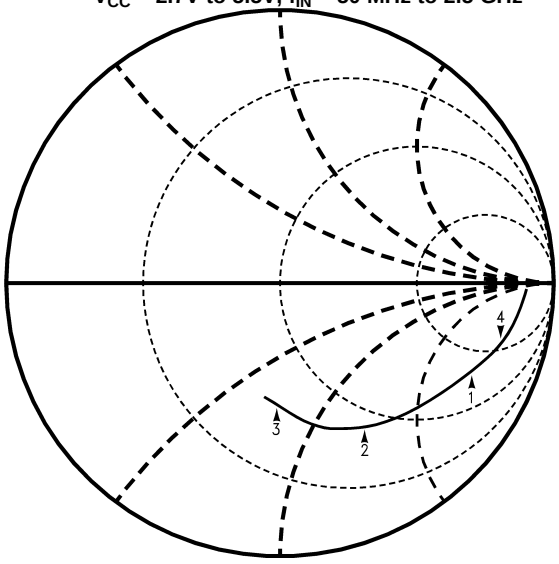
LMX2335L Input Impedance (for TSSOP package)
V_{CC} = 2.7V to 5.5V, f_{IN} = 50 MHz to 1.5 GHz



Marker 1 = 1 GHz, Real = 94, Imaginary = −118
Marker 2 = 1.2 GHz, Real = 72, Imaginary = −88
Marker 3 = 1.5 GHz, Real = 53, Imaginary = −45
Marker 4 = 500 MHz, Real = 201, Imaginary = −224

Figure 11.

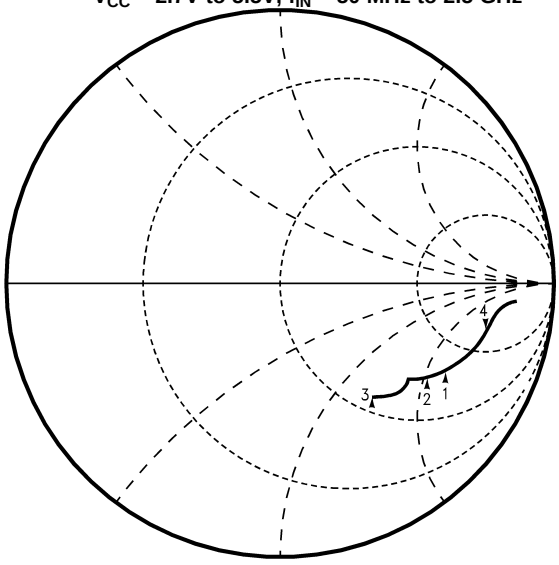
LMX2336L Input Impedance (for TSSOP package)
V_{CC} = 2.7V to 5.5V, f_{IN} = 50 MHz to 2.5 GHz



Marker 1 = 1 GHz, Real = 97, Imaginary = −146
Marker 2 = 1.89 GHz, Real = 43, Imaginary = −67
Marker 3 = 2.5 GHz, Real = 30, Imaginary = −33
Marker 4 = 500 MHz, Real = 189, Imaginary = −233

Figure 12.

LMX2335L Input Impedance (for TSSOP package)
V_{CC} = 2.7V to 5.5V, f_{IN} = 50 MHz to 2.5 GHz

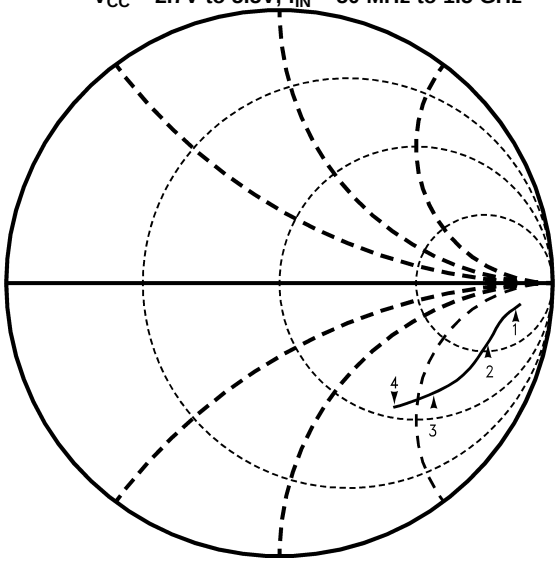


Marker 1 = 1 GHz, Real = 111, Imaginary = −129
Marker 2 = 1.2 GHz, Real = 87, Imaginary = −102
Marker 3 = 1.5 GHz, Real = 61, Imaginary = −70
Marker 4 = 500 MHz, Real = 232, Imaginary = −203

Figure 13.

Typical Performance Characteristics (continued)

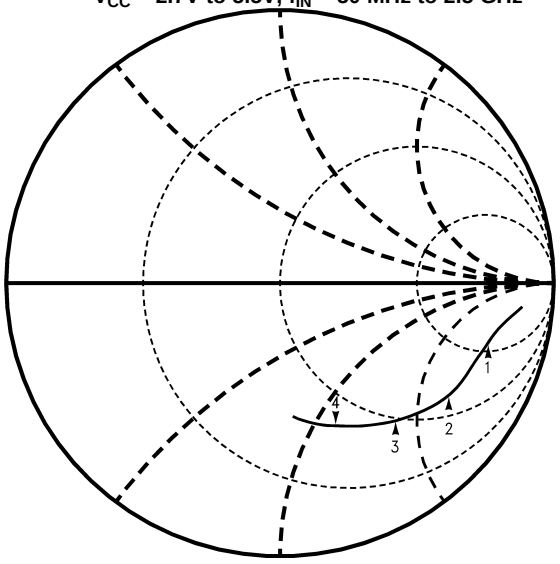
LMX2335L RF/IF PLL, LMX2336 IF PLL (for LGA)
V_{CC} = 2.7V to 5.5V, f_{IN} = 50 MHz to 1.5 GHz



Marker 1 = 100 MHz, 446 −j279 ohm
Marker 2 = 500 MHz, 178 −j210 ohm
Marker 3 = 1500 MHz, 84 −j132 ohm
Marker 4 = 2000 MHz, 54 −j84 ohm

Figure 14.

LMX2336L RF Side (for LGA package)
V_{CC} = 2.7V to 5.5V, f_{IN} = 50 MHz to 2.5 GHz



Marker 1 = 0.5 GHz, 169 −j206 ohm
Marker 2 = 1.0 GHz, 78 −j133 ohm
Marker 3 = 1.5 GHz, 50 −j88 ohm
Marker 4 = 2.0. GHz, 38 −j60 ohm

Figure 15.

I_{DO} TRI-STATE vs D_o Voltage

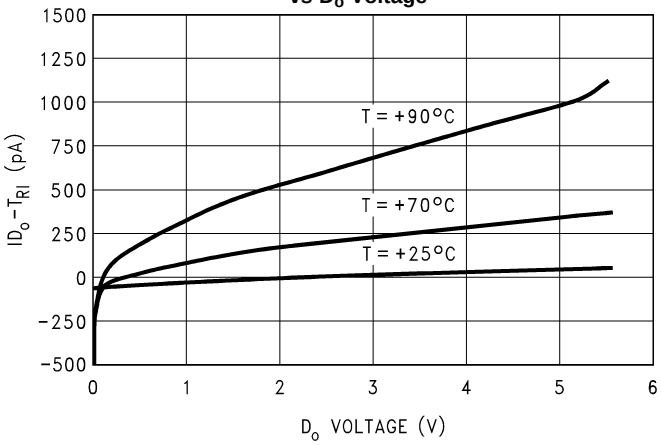


Figure 16.

LMX2335L RF1 Sensitivity vs Frequency

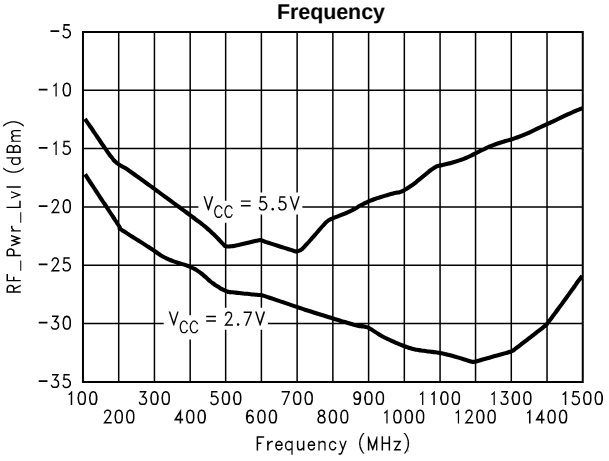


Figure 17.

Typical Performance Characteristics (continued)

LMX2335L RF2 Sensitivity vs Frequency

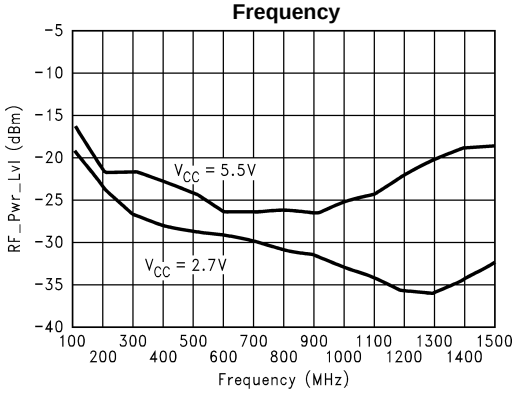


Figure 18.

LMX2336L RF1 Sensitivity vs Frequency

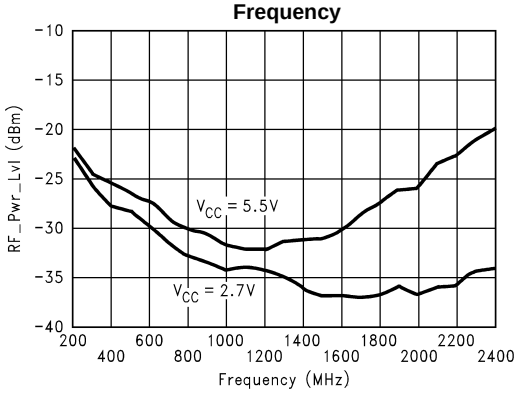


Figure 19.

LMX2336L RF2 Sensitivity vs Frequency

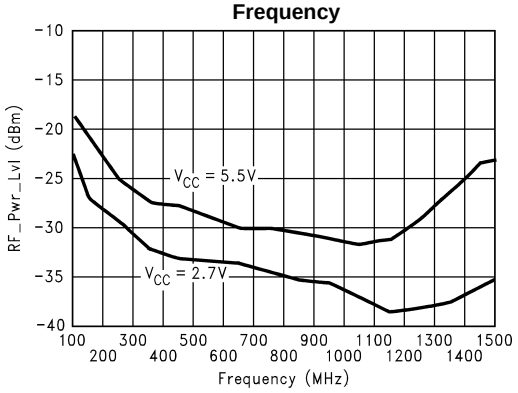


Figure 20.

Oscillator Input Sensitivity vs Frequency

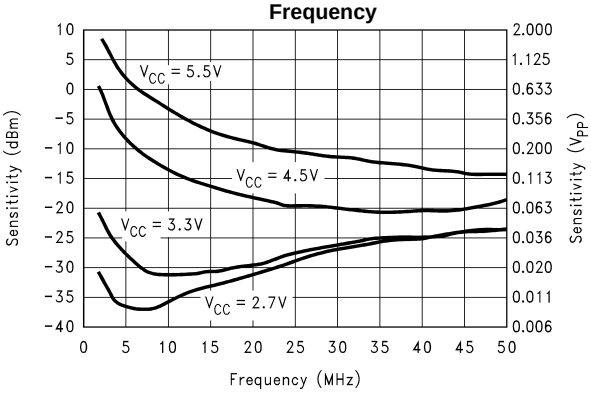


Figure 21.

FUNCTIONAL DESCRIPTION

Figure 22 below shows the 22-bit data register, two 15-bit R Counters and two 18-bit N Counters (intermediate latches are not shown). The data stream is clocked (on the rising edge of Clock) into the DATA register, MSB first. The data stored in the shift register is loaded into one of the 4 appropriate latches on the rising edge of LE. The last two bits are the Control Bits. The DATA is transferred into the counters as follows:

Control Bits		DATA Location
C1	C2	
0	0	RF2 R Counter
0	1	RF1 R Counter
1	0	RF2 N Counter
1	1	RF1 N Counter

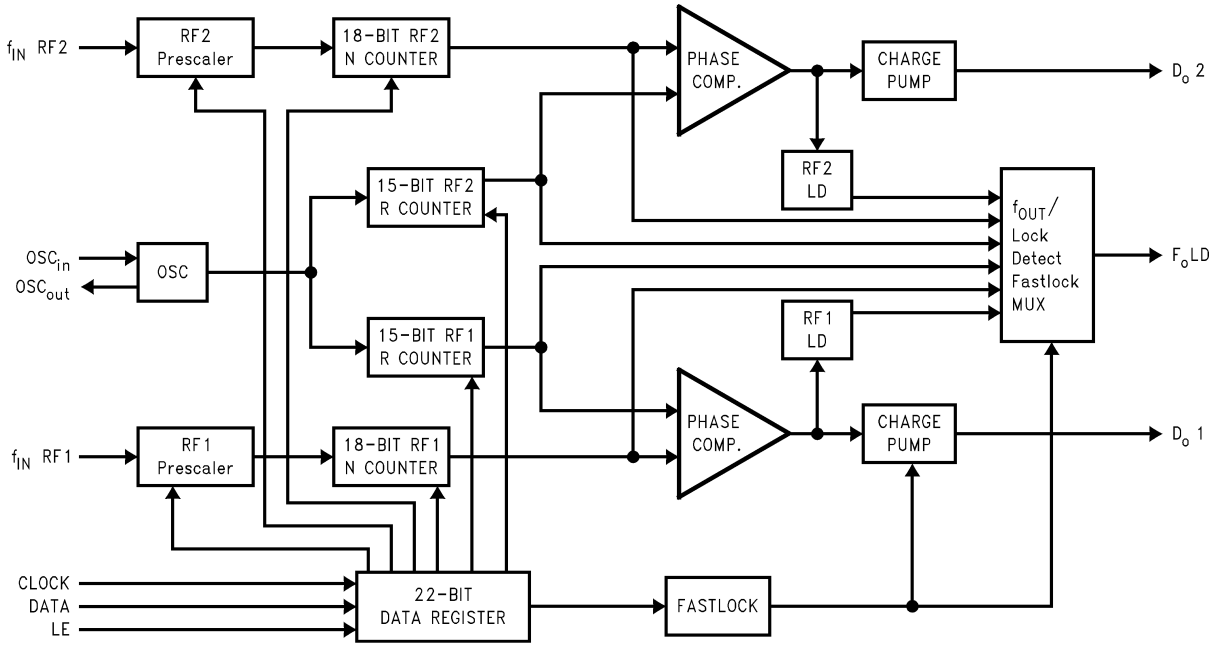
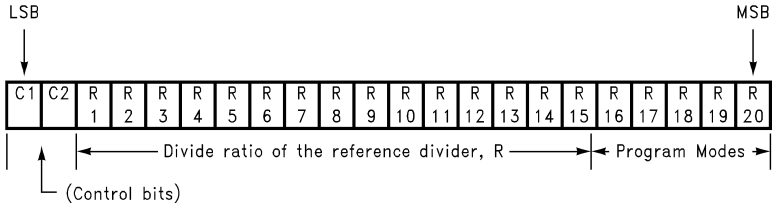


Figure 22.

PROGRAMMABLE REFERENCE DIVIDERS (RF1 AND RF2 R COUNTERS)

If the Control Bits are 00 or 01 (00 for RF2 and 01 for RF1) data is transferred from the 22-bit shift register into a latch which sets the 15-bit R Counter. Serial data format is shown below.



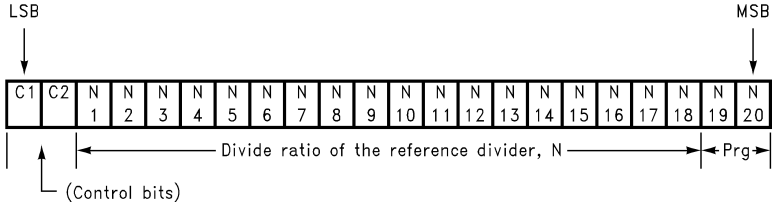
15-BIT PROGRAMMABLE REFERENCE DIVIDER RATIO (R COUNTER)(1)

Divide Ratio	R 15	R 14	R 13	R 12	R 11	R 10	R 9	R 8	R 7	R 6	R 5	R 4	R 3	R 2	R 1
3	0	0	0	0	0	0	0	0	0	0	0	0	0	1	1
4	0	0	0	0	0	0	0	0	0	0	0	0	1	0	0
•	•	•	•	•	•	•	•	•	•	•	•	•	•	•	•
32767	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1

(1) **Notes:**
Divide ratios less than 3 are prohibited.
Divide ratio: 3 to 32767
R1 to R15: These bits select the divide ratio of the programmable reference divider.
Data is shifted in MSB first.

PROGRAMMABLE DIVIDER (N COUNTER)

Each N counter consists of the 7-bit swallow counter (A counter) and the 11-bit programmable counter (B counter). If the Control Bits are 10 or 11 (10 for RF2 counter and 11 for RF1 counter) data is transferred from the 20-bit shift register into a 7-bit latch (which sets the Swallow (A) Counter) and an 11-bit latch (which sets the 11-bit programmable (B) Counter), MSB first. Serial data format is shown below.



7-BIT SWALLOW COUNTER DIVIDE RATIO (A COUNTER)(1)

Divide Ratio A	N 7	N 6	N 5	N 4	N 3	N 2	N 1
0	0	0	0	0	0	0	0
1	0	0	0	0	0	0	1
•	•	•	•	•	•	•	•
127	1	1	1	1	1	1	1

(1) **Notes:**
Divide ratio: 0 to 127
B ≥ A
A < P

11-BIT PROGRAMMABLE COUNTER DIVIDE RATIO (B COUNTER)(1)

Divide Ratio B	N 18	N 17	N 16	N 15	N 14	N 13	N 12	N 11	N 10	N 9	N 8
3	0	0	0	0	0	0	0	0	0	1	1
4	0	0	0	0	0	0	0	0	1	0	0
•	•	•	•	•	•	•	•	•	•	•	•
2047	1	1	1	1	1	1	1	1	1	1	1

(1) **Note:**
Divide ratio: 3 to 2047 (Divide ratios less than 3 are prohibited)
B ≥ A

PULSE SWALLOW FUNCTION

$f_{VCO} = [(P \times B) + A] \times f_{OSC}/R$

f_{VCO}: Output frequency of external voltage controlled oscillator (VCO)

B: Preset divide ratio of binary 11-bit programmable counter (3 to 2047)

A: Preset divide ratio of binary 7-bit swallow counter

(0 ≤ A ≤ P; A ≤ B)

f_{OSC}: Output frequency of the external reference frequency oscillator

R: Preset divide ratio of binary 15-bit programmable reference counter (3 to 32767)

P: Preset modulus of dual modulus prescaler (P = 64 or 128)

PROGRAMMABLE MODES

Several modes of operation can be programmed with bits R16–R20 including the phase detector polarity, charge pump tristate and the output of the F_oLD pin. The prescaler and power down modes are selected with bits N19 and N20. The programmable modes are shown in Table 1. Truth table for the programmable modes and F_oLD output are shown in Table 2 and Table 3.

Table 1. Programmable Modes

C1	C2	R16	R17	R18	R19	R20
0	0	RF2 Phase Detector Polarity	RF2 I_{CPo}	RF2 D_o TRI-STATE	RF2 LD	RF2 F_o
0	1	RF1 Phase Detector Polarity	RF1 I_{CPo}	RF1 D_o TRI-STATE	RF1 LD	RF1 F_o

C1	C2	N19	N20
1	0	RF2 Prescaler	Pwdn RF2
1	1	RF1 Prescaler	Pwdn RF1

Table 2. Mode Select Truth Table

	Phase Detector Polarity (1)	D_o TRI-STATE (2)	I_{CPo} (3)	RF1 Prescaler	RF2 Prescaler	Pwdn (2)
0	Negative	Normal Operation	LOW	64/65	64/65	pwrd up
1	Positive	TRI-STATE	HIGH	128/129	128/129	pwrd dn

(1) PHASE DETECTOR POLARITY, Depending upon VCO characteristics, R16 bit should be set accordingly: (see Figure 23) When VCO characteristics are positive like (1), R16 should be set HIGH; When VCO characteristics are negative like (2), R16 should be se LOW.
(2) Refer to POWERDOWN OPERATION.
(3) The I_{CPo} LOW current state = 1/4 × I_{CPo} HIGH current.

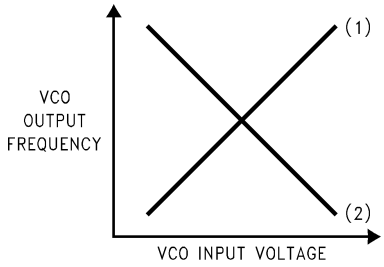


Figure 23. VCO Characteristics

Table 3. The F_oLD Output Truth Table(1)

RF1 R[19] (RF1 LD)	RF2 R[19] (RF2 LD)	RF1 R[20] (RF1 F_O)	RF2 R[20] (RF2 F_O)	F_oLD Output State
0	0	0	0	Disabled (2)
0	1	0	0	RF2 Lock Detect (3)
1	0	0	0	RF1 Lock Detect (3)
1	1	0	0	RF1/RF2 Lock Detect (3)
X	0	0	1	RF2 Reference Divider Output
X	0	1	0	RF1 Reference Divider Output
X	1	0	1	RF2 Programmable Divider Output
X	1	1	0	RF1 Programmable Divider Output
0	0	1	1	Fastlock (4)
0	1	1	1	RF2 Counter Reset (5)
1	0	1	1	RF1 Counter Reset (5)
1	1	1	1	RF1 and RF2 Counter Reset (5)

(1) X—don't care condition
(2) When the F_oLD output is disabled it is actively pulled to a low logic state.
(3) Lock detect output provided to indicate when the VCO frequency is in “lock”. When the loop is locked and a lock detect mode is selected, the pins output is HIGH, with narrow pulses LOW. In the RF1/RF2 lock detect mode a locked condition is indicated when RF2 and RF1 are both locked.
(4) The Fastlock mode utilized the F_oLD output pin to switch a second loop filter damping resistor to ground during fastlock operation. Activation of Fastlock occurs whenever the RF loop's Icpo magnitude bit #17 is selected HIGH (while the #19 and #20 mode bits are set for Fastlock).
(5) The RF2 counter reset mode resets RF2 PLL's R and N counters and brings RF2 charge pump output to a TRI-STATE condition. The RF1 counter reset mode resets RF1 PLL's R and N counters and brings RF1 charge pump output to a TRI-STATE condition. The RF1 and RF2 counter reset mode resets all counters and brings both charge pump output to a TRI-STATE condition. Upon removal of the Reset bits the N counter resumes counting in “close” alignment with the R counter. (The maximum error is one prescaler cycle).

POWERDOWN OPERATION

Synchronous and asynchronous powerdown modes are both available by microwire selection. Synchronously powerdown occurs if the respective loop's R18 bit (Do TRI-STATE) is LOW when its N20 bit (Pwdn) becomes HI. Asynchronous powerdown occurs if the loop's R18 bit is HI when its N20 bit becomes HI.

In the synchronous powerdown mode, the powerdown function is gated by the charge pump to prevent unwanted frequency jumps. Once the powerdown program bit N20 is loaded, the part will go into powerdown mode when the charge pump reaches a TRI-STATE condition.

In the asynchronous powerdown mode, the device powers down immediately after the LE pin latches in a HI condition on the powerdown bit N20.

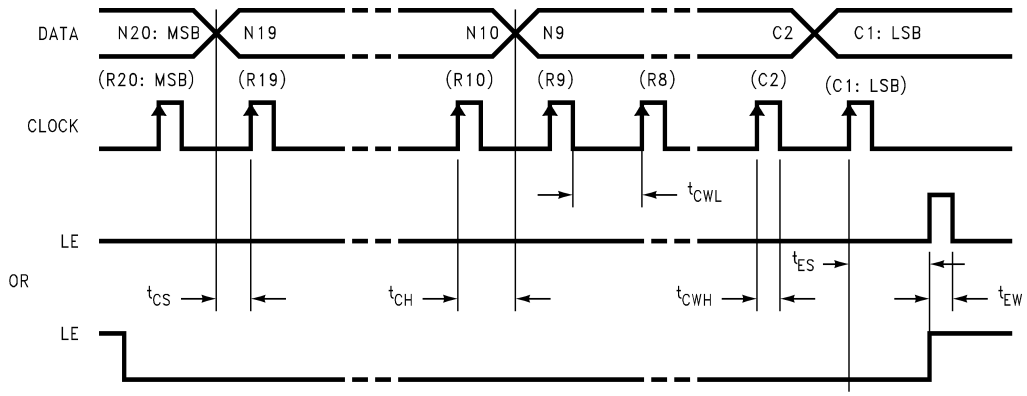
Activation of either the IF or RF PLL powerdown conditions in either synchronous or asynchronous modes forces the respective loop's R & N dividers to their load state condition and debiasing of it's respective Fin input to a high impedance state. The oscillator circuitry function does not become disabled until both IF and RF powerdown bits are activated. The MICROWIRE control register remains active and capable of loading and latching data during all of the powerdown modes.

The device returns to an actively powered up condition in either synchronous ar asynchronous modes immediately upon LE latching LOW data into bit N20.

Table 4. Powerdown Mode Select Table

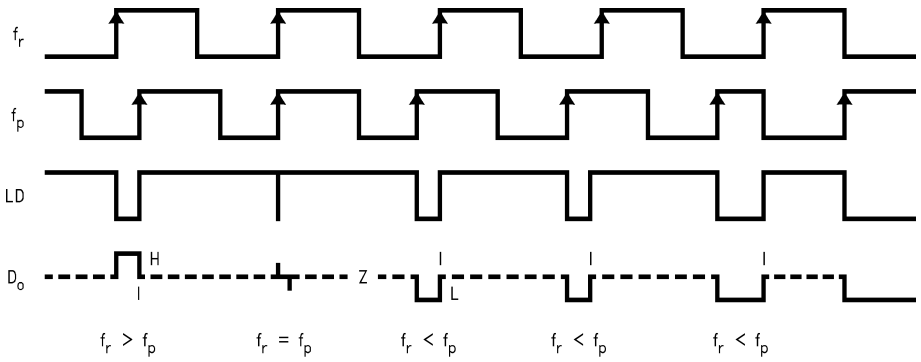
R18	N20	Powerdown Status
0	0	PLL Active
1	0	PLL Active (Charge Pump Output TRI-STATE)
0	1	Synchronous Powerdown Initiated
1	1	Asynchronous Powerdown Initiated

SERIAL DATA INPUT TIMING



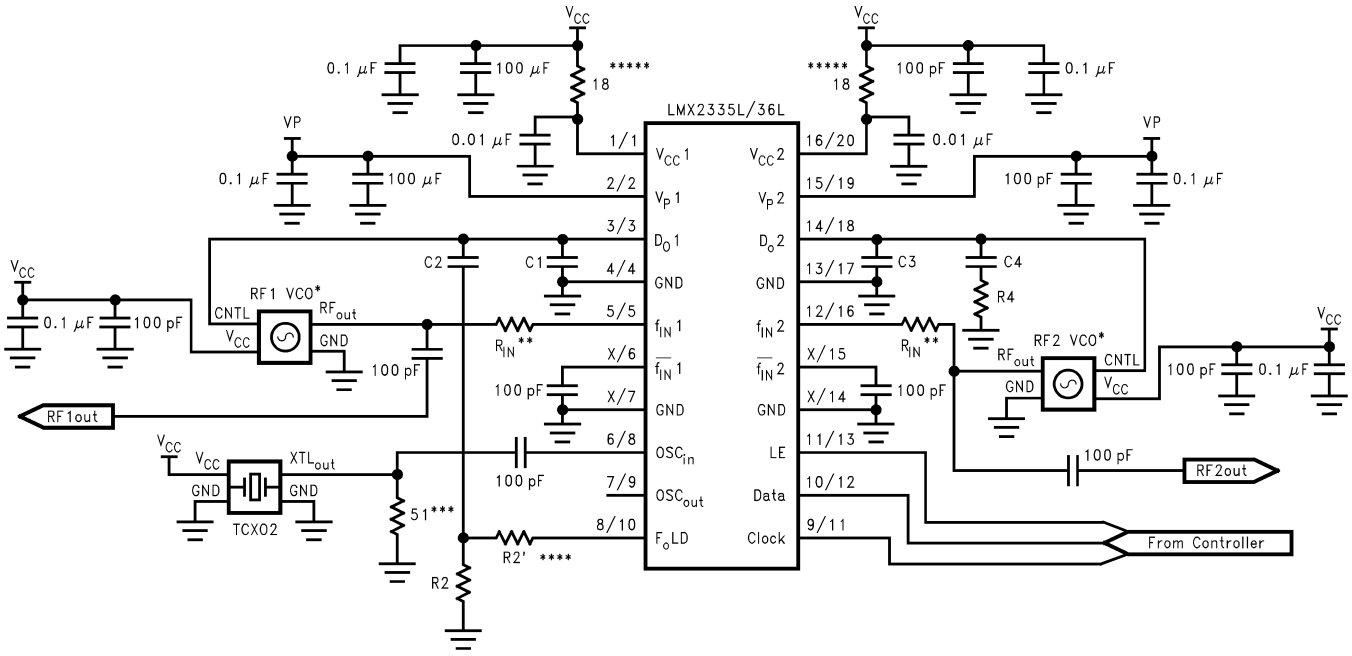
Parenthesis data indicates programmable reference divider data.
Data shifted into register on clock rising edge.
Data is shifted in MSB first.
t_{CS} = Data to Clock Set Up Time
t_{CH} = Data to Clock Hold Time
t_{CWH} = Clock Pulse Width High
t_{CWL} = Clock Pulse Width Low
t_{ES} = Clock to Load Enable Set Up Time
t_{EW} = Load Enable Pulse Width
Test Conditions: The Serial Data Input Timing is tested using a symmetrical waveform around $V_{CC}/2$. The test waveform has an edge rate of 0.6V/ns with amplitudes of 2.2V @ V_{CC} = 2.7V and 2.6V @ V_{CC} = 5.5V.

PHASE COMPARATOR AND INTERNAL CHARGE PUMP CHARACTERISTICS



Notes: Phase difference detection range: −2π to +2π
The minimum width pump up and pump down current pulses occur at the D_o pin when the loop is locked.

Typical Application Example



Operational Notes:

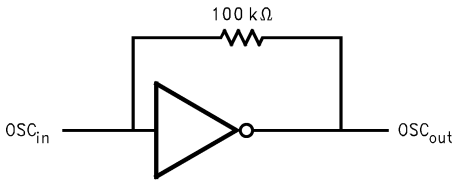
***** VCO is assumed AC coupled.

****** R_{IN} increases impedance so that VCO output power is provided to the load rather than the PLL. Typical values are 10Ω to 200Ω depending on the VCO power level. f_{IN} RF impedance ranges from 40Ω to 100Ω. f_{IN} IF impedances are higher.

******* 50Ω termination is often used on test boards to allow use of external reference oscillator. For most typical products a CMOS clock is used and no terminating resistor is required. OSC_{in}may be AC or DC coupled. AC coupling is recommended because the input circuit provides its own bias. (See Figure 24).

******** R2 configured F_oLD for use in FastLock mode.

********* Adding RC filters to the V_{CC} lines is recommended to reduce loop-to-loop noise coupling.



Application Hints:

Proper use of grounds and bypass capacitors is essential to achieve a high level of performance. Crosstalk between pins can be reduced by careful board layout.

This is an electrostatic sensitive device. It should be handled only at static free work stations.

Figure 24.

Application Information

A block diagram of the basic phase locked loop is shown in Figure 25.

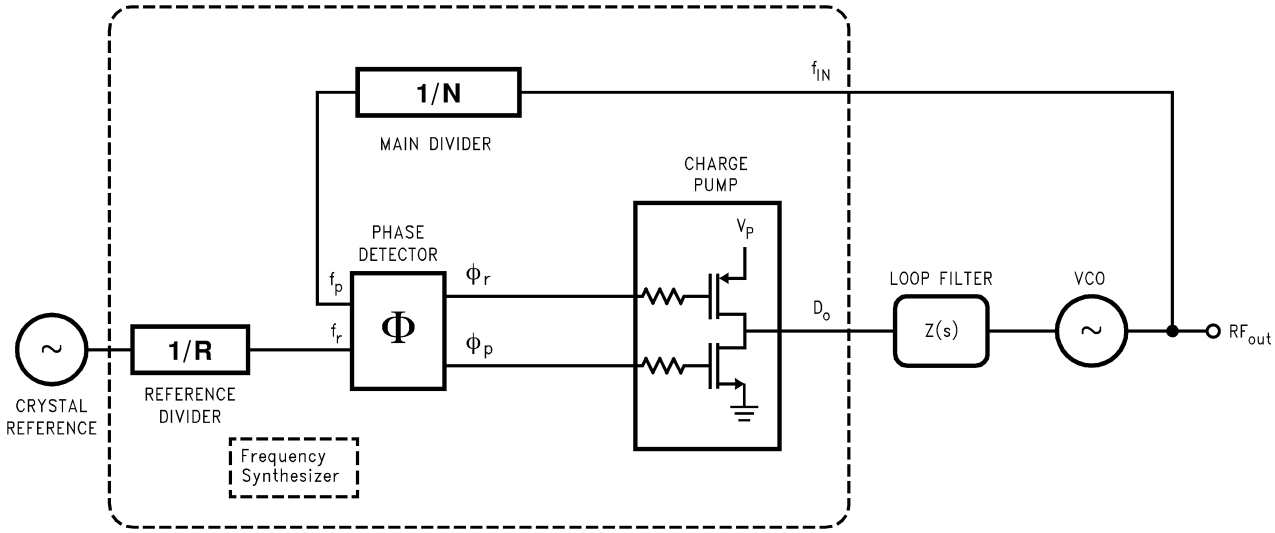


Figure 25. Conventional PLL Architecture

LOOP GAIN EQUATIONS

A linear control system model of the phase feedback for a PLL in the locked state is shown in Figure 26. The open loop gain is the product of the phase comparator gain (K_ϕ), the VCO gain (K_{VCO}/s), and the loop filter gain Z(s) divided by the gain of the feedback counter modulus (N). The passive loop filter configuration used is displayed in Figure 27, WHILE the complex impedance of the filter is given in equation 2.

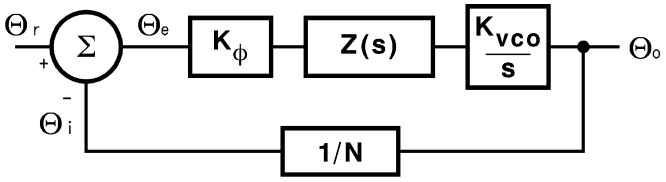


Figure 26. PLL Linear Model

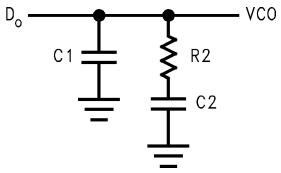


Figure 27. Passive Loop Filter

$$\text{Open Loop Gain} = H(s)\,G(s) = \frac{\Theta i}{\Theta e} = \frac{K_\phi Z(s)\,K_{VCO}}{Ns} \quad (1)$$

$$Z(s) = \frac{s(C2 \bullet R2) + 1}{S^2 (C1 \bullet C2 \bullet R2) + sC1 + sC2} \quad (2)$$

The time constants which determine the pole and zero frequencies of the filter transfer function can be defined as

$$T1 = R2 \bullet \frac{C1 \bullet C2}{C1 + C2}$$

$$T2 = R2 \bullet C2 \quad (3)$$

The 3rd order PLL Open Loop Gain can be calculated in terms of frequency, ω, the filter time contants T1 and T2, and the design constants Kφ, K_{VCO}, and N.

$$G(s) \bullet H(s) \mid_{S = j \bullet w} = \frac{-K_{\phi} \bullet K_{VCO} (1 + jw \bullet T2)}{w^2 C1 \bullet N (1 + jw \bullet T1)} \bullet \frac{T1}{T2} \quad (4)$$

From Equation 3 we can see that the phase term will be dependent on the single pole and zero such that the phase margin is determined in Equation 1.

$$\varphi(\omega) = \tan^{-1} (\omega \bullet T2) - \tan^{-1} (\omega \bullet T1) + 180°C \quad (5)$$

A plot of the magnitude and phase of G(s) H(s) for a stable loop, is shown in Equation 4 with a solid trace. The parameter φ_p shows the amount of phase margin that exists at the point the gain drops below zero (the cutoff frequency wp of the loop). In a critically damped system, the amount of phase margin would be approximately 45 degrees.

If we were now to redefine the cut off frequency, wp', as double the frequency which gave us our original loop bandwidth, wp, the loop response time would be approximately halved. Because the filter attenuation at the comparison frequency also diminishes, the spurs would have increased by approximately 6 dB. In the proposed Fastlock scheme, the higher spur levels and wider loop filter conditions would exist only during the initial lock-on phase—just long enough to reap the benefits of locking faster. The objective would be to open up the loop bandwidth but not introduce any additional complications or compromises related to our original design criteria. We would ideally like to momentarily shift the curve Figure 28 over to a different cutoff frequency, illustrated by dotted line, without affecting the relative open loop gain and phase relationships. To maintain the same gain/phase relationship at twice the original cutoff frequency, other terms in the gain and phase equations 4 and 5 will have to compensate by the corresponding “1/w” or “1/w^2” factor. Examination of equations 3 and 5 indicates the damping resistor variable R2 could be chosen to compensate with “w” terms for the phase margin. This implies that another resistor of equal value to R2 will need to be switched in parallel with R2 during the initial lock period. We must also insure that the magnitude of the open loop gain, H(s)G(s) is equal to zero at wp' = 2 wp. K_{VCO}, Kφ, N, or the net product of these terms can be changed by a factor of 4, to counteract with w^2 term present in the denominator of equation 3. The Kφ term was chosen to complete the transformation because it can readily be switched between 1X and 4X values. This is accomplished by increasing the charge pump output current from 1 mA in the standard mode to 4 mA in Fastlock.

FASTLOCK CIRCUIT IMPLEMENTATION

A diagram of the Fastlock scheme as implemented in Texas Instruments LMX2335L/36L PLL is shown in Figure 29. When a new frequency is loaded, and the RF1 I_{CPo} bit is set high, the charge pump circuit receives an input to deliver 4 times the normal current per unit phase error while an open drain NMOS on chip device switches in a second R2 resistor element to ground. The user calculates the loop filter component values for the normal steady state considerations. The device configuration ensures that as long as a second identical damping resistor is wired in appropriately, the loop will lock faster without any additional stability considerations to account for. Once locked on the correct frequency, the user can return the PLL to standard low noise operation by sending a MICROWIRE instruction with the RF1 I_{CPo} bit set low. This transition does not affect the charge on the loop filter capacitors and is enacted synchronous with the charge pump output. This creates a nearly seamless change between Fastlock and standard mode.

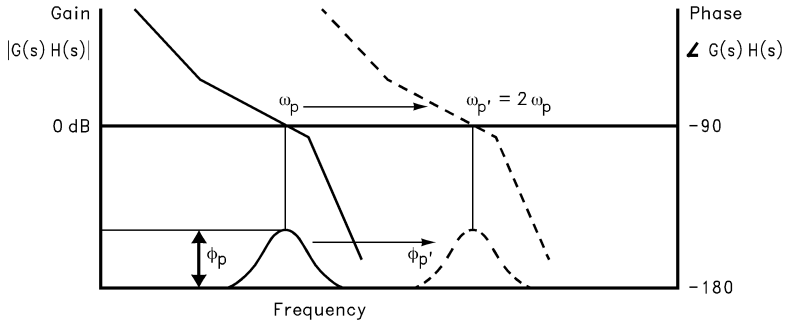


Figure 28. Open Loop Response Bode Plot

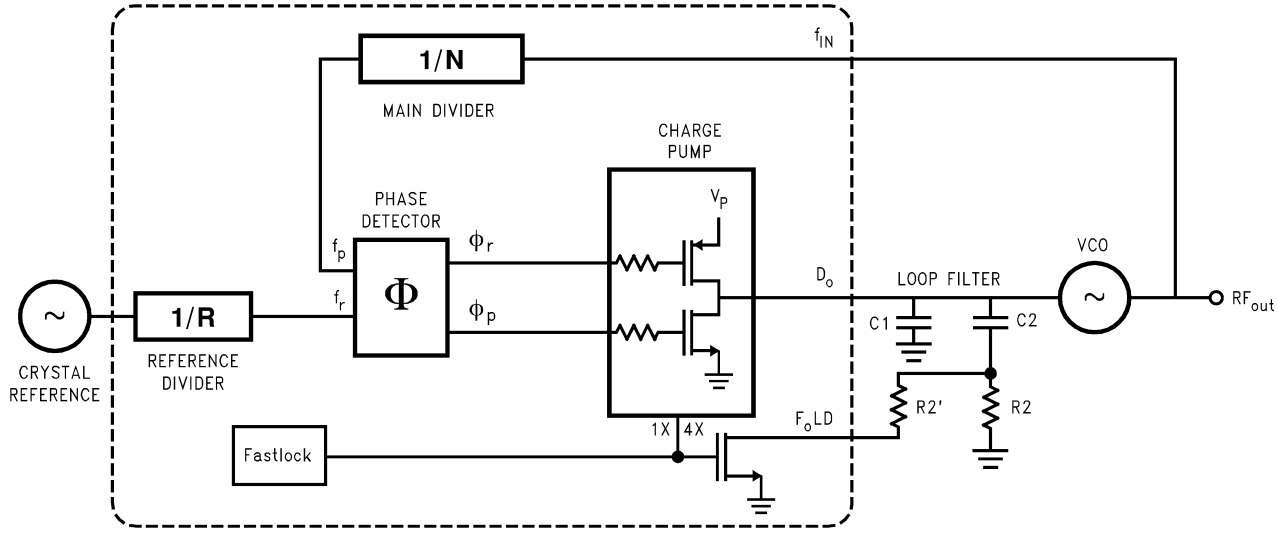


Figure 29. Fastlock PLL Architecture

REVISION HISTORY

Changes from Revision C (March 2013) to Revision D	Page
• Changed layout of National Data Sheet to TI format	21

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